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ABSTRACT

Provided is a manufacturing process for an annealed wafer capable of elucidating a relationship between a tilt angle from a (100) plane of a wafer to be annealed and haze to set optimal tilt angles for suppression of haze and to improve a characteristic of a device from the annealed wafer as a result of the suppression of haze. A silicon mirror wafer having a surface orientation with a tilt angle in the range of 0.1 degree $< \theta <$ 0.2 degree from a (100) plane or a plane equivalent thereto is heat treated in an atmosphere of hydrogen gas, an inert gas, nitrogen gas or a mixed gas thereof.